

# Narihito Okada

## List of Publications by Year in descending order

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52  
papers

679  
citations

686830

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h-index

580395

25  
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all docs

52  
docs citations

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times ranked

658  
citing authors

#	ARTICLE	IF	CITATIONS
1	Three-dimensional curving of crystal planes in wide bandgap semiconductor wafers visualized using a laboratory X-ray diffractometer. <i>Journal of Crystal Growth</i> , 2022, 583, 126558.	0.7	2
2	Investigation of off-cut angle of sapphire for epitaxial lateral overgrowth of AlN and fabrication of high-quality AlN template. <i>Journal of Crystal Growth</i> , 2022, 588, 126640.	0.7	6
3	Observation of threading dislocations with a c+m type Burgers vector in HVPE GaN substrates using multi-photon excitation photoluminescence and TEM. <i>Journal of Crystal Growth</i> , 2022, , 126748.	0.7	0
4	Study on higher-energy emission observed locally around V-pits on InGaN/GaN quantum wells grown on moderate-temperature GaN. <i>Journal of Applied Physics</i> , 2021, 130, 053103.	1.1	0
5	Deep ultraviolet emission from multiple quantum wells on flat N-polar AlN templates fabricated using periodical pulsed H <sub>2</sub> etching. <i>Japanese Journal of Applied Physics</i> , 2021, 60, 125502.	0.8	4
6	Anisotropic radius of curvature of crystal planes in wide-bandgap semiconductor wafers measured by X-ray diffraction. <i>Japanese Journal of Applied Physics</i> , 2021, 60, 128004.	0.8	2
7	Correlation between structural properties and nonradiative recombination behaviors of threading dislocations in freestanding GaN substrates grown by hydride vapor phase epitaxy. <i>CrystEngComm</i> , 2020, 22, 8299-8312.	1.3	13
8	Study of dislocations in AlN single-crystal using bright-field synchrotron x-ray topography under a multiple-beam diffraction condition. <i>Applied Physics Letters</i> , 2020, 117, 092102.	1.5	4
9	Growth and Characterization of Nitrogen-Polar AlGaIn/AlN Heterostructure for High-Electron-Mobility Transistor. <i>Physica Status Solidi (B): Basic Research</i> , 2020, 257, 1900589.	0.7	13
10	Effect of InGaN/GaN Superlattice on Lattice Curvature of GaN Layers Grown on Sapphire Substrates. <i>Physica Status Solidi (B): Basic Research</i> , 2020, 257, 1900586.	0.7	1
11	Growth of N-Polar Aluminum Nitride on Vicinal Sapphire Substrates and Aluminum Nitride Bulk Substrates. <i>Physica Status Solidi (B): Basic Research</i> , 2020, 257, 1900588.	0.7	17
12	High-quality GaN crystals grown from double-polarity hydride vapor phase epitaxy and single-polarization regrowth. <i>Japanese Journal of Applied Physics</i> , 2019, 58, SC1019.	0.8	0
13	Growth of GaN and improvement of lattice curvature using symmetric hexagonal SiO <sub>2</sub> patterns in HVPE growth. <i>Japanese Journal of Applied Physics</i> , 2019, 58, SC1049.	0.8	6
14	Observation of dislocations and their arrays in physical vapor transport-grown AlN single-crystal substrate by synchrotron X-ray topography. <i>Japanese Journal of Applied Physics</i> , 2019, 58, SCCB29.	0.8	10
15	Effect of off-angle of stripe patterns on facet stability and embedding in selective-area hydride vapor phase epitaxy growth. <i>Japanese Journal of Applied Physics</i> , 2019, 58, SC1001.	0.8	0
16	Separation of effects of InGaN/GaN superlattice on performance of light-emitting diodes using mid-temperature-grown GaN layer. <i>Japanese Journal of Applied Physics</i> , 2018, 57, 062101.	0.8	13
17	Spatially Resolved Spectroscopy of Blue and Green InGaN Quantum Wells by Scanning Near-Field Optical Microscopy. <i>Physica Status Solidi (B): Basic Research</i> , 2018, 255, 1700322.	0.7	3
18	Potential Barrier Formed Around Dislocations in InGaN Quantum Well Structures by Spot Cathodoluminescence Measurements. <i>Physica Status Solidi (B): Basic Research</i> , 2018, 255, 1700358.	0.7	13

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19	Impact of thermal treatment on the growth of semipolar AlN on <i>c</i> -plane sapphire. AIP Advances, 2018, 8, .	0.6	12
20	Nanoscope spectroscopy of potential barriers formed around V-pits in InGaN/GaN multiple quantum wells on moderate temperature GaN pit expansion layers. Journal of Applied Physics, 2018, 124, .	1.1	7
21	Mechanism for the formation of nitrogen-filled voids after annealing of GaN on a sapphire substrate. Journal of Applied Physics, 2018, 124, .	1.1	4
22	Direct observation of inclined a-type threading dislocation with a-type screw dislocation in GaN. Journal of Applied Physics, 2017, 121, 185101.	1.1	7
23	Visualization of dislocation behavior in HVPE-grown GaN using facet controlling techniques. Physica Status Solidi (B): Basic Research, 2017, 254, 1600716.	0.7	6
24	Bulk GaN substrate with overall dislocation density on the order of 10 <sup>5</sup> /cm <sup>2</sup> fabricated by hydride vapor phase epitaxy. Journal of Crystal Growth, 2017, 478, 123-128.	0.7	21
25	V-shaped pits in HVPE-grown GaN associated with columnar inversion domains originating from foreign particles of $\pm$ -Si <sub>3</sub> N <sub>4</sub> and graphitic carbon. Micron, 2017, 94, 9-14.	1.1	4
26	Alternately double-sided growth of low-curvature GaN templates on sapphire substrates using hydride vapor phase epitaxy. Physica Status Solidi (B): Basic Research, 2016, 253, 819-823.	0.7	3
27	Origin of lattice bowing of freestanding GaN substrates grown by hydride vapor phase epitaxy. Journal of Applied Physics, 2016, 119, .	1.1	16
28	Growth of semipolar {20 $\bar{1}$ 1} GaN and {20 $\bar{2}$ 1} GaN for GaN substrate. Physica Status Solidi (B): Basic Research, 2016, 253, 36-45.	0.7	1
29	Effect of superlattice on light output power of InGaN-based light-emitting diodes fabricated on underlying GaN substrates with different dislocation densities. Physica Status Solidi C: Current Topics in Solid State Physics, 2016, 13, 270-273.	0.8	5
30	Thickness and growth condition dependence of crystallinity in semipolar (20 $\bar{1}$ 1) GaN films grown on (22 $\bar{4}$ 3) patterned sapphire substrates. Physica Status Solidi (B): Basic Research, 2015, 252, 1142-1148.	0.7	5
31	Crystalline property analysis of semipolar (20 $\bar{1}$ 1) GaN on (22 $\bar{4}$ 3) patterned sapphire substrate by X-ray microdiffraction and transmission electron microscopy. Physica Status Solidi (B): Basic Research, 2015, 252, 1149-1154.	0.7	6
32	Controlling potential barrier height by changing V-shaped pit size and the effect on optical and electrical properties for InGaN/GaN based light-emitting diodes. Journal of Applied Physics, 2015, 117, .	1.1	40
33	WeC-2-1 Transmission electron microscopy study on origin of threading dislocations in GaN layer grown on patterned sapphire substrate. Proceedings of JSME-IIP/ASME-ISPS Joint Conference on Micromechanics for Information and Precision Equipment IIP/ISPS Joint MIPE, 2015, 2015, WeC-2-1-1- WeC-2-1-3.	0.0	0
34	Fabrication of freestanding {20 $\bar{1}$ 1} GaN substrates by HVPE using SiO <sub>2</sub> masked GaN templates. Physica Status Solidi C: Current Topics in Solid State Physics, 2014, 11, 401-404.	0.8	6
35	Epitaxial lateral overgrowth of thick semipolar {11 $\bar{2}$ 0} GaN by hydride vapor phase epitaxy. Physica Status Solidi C: Current Topics in Solid State Physics, 2014, 11, 549-552.	0.8	0
36	Characterization of semipolar {11 $\bar{2}$ 0} light-emitting diodes using a hole blocking layer. Physica Status Solidi C: Current Topics in Solid State Physics, 2014, 11, 775-777.	0.8	2

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37	S1660104 Optimal design of the patterned sapphire substrate from viewpoints of light extraction efficiency and crystalline quality of light emitting diodes. The Proceedings of Mechanical Engineering Congress Japan, 2014, 2014, _S1660104--_S1660104-.	0.0	0
38	I-1-3 Etching of nano-patterned sapphire substrates using chf_3 and BCL_3 inductively coupled plasmas. The Proceedings of the Conference on Information Intelligence and Precision Equipment IIP, 2013, 2013, 8-12.	0.0	0
39	Green light-emitting diodes fabricated on semipolar (11 $\bar{2}$ ) GaN on c-plane patterned sapphire substrate. Physica Status Solidi (A) Applications and Materials Science, 2012, 209, 469-472.	0.8	21
40	Growth of {11 $\bar{2}$ } GaN on shallowly etched c-plane patterned sapphire substrates. Physica Status Solidi C: Current Topics in Solid State Physics, 2012, 9, 568-571.	0.8	8
41	Behavior of misfit dislocations in semipolar InGaN/GaN grown by MOVPE. Physica Status Solidi C: Current Topics in Solid State Physics, 2012, 9, 488-491.	0.8	6
42	Growth of semipolar {10 $\bar{1}$ } GaN from c-plane-like sapphire sidewall of patterned n-plane sapphire substrate. Physica Status Solidi C: Current Topics in Solid State Physics, 2011, 8, 2101-2103.	0.8	15
43	Characterization of semipolar (11 $\bar{2}$ ) GaN on c-plane sapphire sidewall of patterned r-plane sapphire substrate without SiO <sub>2</sub> mask. Physica Status Solidi C: Current Topics in Solid State Physics, 2010, 7, 2059-2062.	0.8	5
44	Evaluation of multiple-quantum-well structure on InGaN template using (11 $\bar{2}$ ) facet growth and mass transport. Physica Status Solidi C: Current Topics in Solid State Physics, 2010, 7, 2063-2065.	0.8	4
45	Growth mechanism of nonpolar m-plane GaN on maskless patterned a-plane sapphire substrate. Physica Status Solidi C: Current Topics in Solid State Physics, 2010, 7, 2066-2068.	0.8	2
46	Light-emitting diodes fabricated on nanopatterned sapphire substrates by thermal lithography. Physica Status Solidi C: Current Topics in Solid State Physics, 2010, 7, 2165-2167.	0.8	15
47	Growth of m-GaN layers by epitaxial lateral overgrowth from sapphire sidewalls. Physica Status Solidi (A) Applications and Materials Science, 2009, 206, 1164-1167.	0.8	12
48	High-efficiency AlGaIn-based UV light-emitting diode on laterally overgrown AlN. Journal of Crystal Growth, 2008, 310, 2326-2329.	0.7	54
49	Impact of high-temperature growth by metal-organic vapor phase epitaxy on microstructure of AlN on 6H-SiC substrates. Journal of Crystal Growth, 2008, 310, 2308-2313.	0.7	65
50	Dislocations in AlN Epilayers Grown on Sapphire Substrate by High-Temperature Metal-Organic Vapor Phase Epitaxy. Japanese Journal of Applied Physics, 2007, 46, 1458-1462.	0.8	90
51	Epitaxial lateral overgrowth of AlN on trench-patterned AlN layers. Journal of Crystal Growth, 2007, 298, 257-260.	0.7	104
52	Thermodynamic Aspects of Growth of AlGaIn by High-Temperature Metal Organic Vapor Phase Epitaxy. Japanese Journal of Applied Physics, 2006, 45, 2502-2504.	0.8	26